

## AMENDMENTS

This listing of claims replaces all prior versions, and listings, of claims in the application:

### In the Claims:

1-25. (Cancelled)

26. (Currently Amended) A method of fabricating a nitride semiconductor device, comprising the steps of:

~~adjusting to within a range from 80 to 160  $\mu$ m a thickness of~~ forming a nitride semiconductor wafer ~~formed by depositing on a substrate that exhibits cleavage a nitride semiconductor layer formed out of~~ comprising a compound containing a group III element and nitrogen and ~~including, having~~ a cleavage plane crystallographically similar ~~[[equal]]~~ to a cleavage plane of the substrate~~[[, with]]~~ and comprising a plurality of stripe-shaped optical waveguides formed at an equal intervals separation in the nitride semiconductor layer;

adjusting a thickness of the nitride semiconductor wafer so that the thickness falls within a range from 80 to 160  $\mu$ m;

forming a plurality of cleavage guide grooves in a shape of discontinuous broken lines in a top surface of the nitride semiconductor wafer by scribing from above the nitride semiconductor layer ~~in such a way so~~ that the cleavage guide grooves reach the substrate and no cleavage guide groove extends over the stripe-shaped optical wave guides; and

cleaving the nitride semiconductor wafer along the cleavage guide grooves;

~~wherein the cleavage guide grooves are formed elsewhere than right above the stripe-shaped optical waveguides.~~

27. (Currently Amended) ~~[[A]]~~ The method of fabricating a nitride semiconductor device ~~as claimed in~~ of claim 26, wherein the substrate ~~[[is]]~~ comprises a nitride semiconductor

substrate ~~formed out of~~ comprising ~~[[a]]~~ another compound containing a group III element and nitrogen.

28. (Currently Amended) ~~[[A]]~~ The method of fabricating a nitride semiconductor device ~~as claimed in~~ of claim 26, wherein a ~~depth~~ distance from the top surface of the nitride semiconductor wafer to bottoms of the cleavage guide grooves is ~~within a range~~  $1 \leq d \leq$  equal to or larger than  $1 \mu\text{m}$  and equal to or smaller than  $10 \mu\text{m}$ .

29. (Currently Amended) ~~[[A]]~~ The method of fabricating a nitride semiconductor device ~~as claimed in~~ of claim 28, wherein the forming of the cleavage guide grooves ~~[[are]]~~ is such that the cleavage guide grooves are discontinuous in a same broken line with an equal interval ~~formed with intervals of 1 mm or shorter left between every two adjacent ones thereof on a same broken line.~~

30-37. (Cancelled)

38. (Currently Amended) ~~[[A]]~~ The method of fabricating a nitride semiconductor device ~~as claimed in~~ of claim 26, wherein, ~~when a semiconductor layer of a material that cleaves in a different direction from the nitride semiconductor is formed at an interface between the nitride semiconductor layer and the substrate,~~ further comprising forming ~~[[first]]~~ a plurality of cleavage assist grooves ~~are formed~~ in a shape of discontinuous broken lines in ~~[[a]]~~ the top surface of the nitride semiconductor ~~[[layer]]~~ wafer so as to a depth reaching reach half a thickness of the nitride semiconductor layer by scribing from above the top surface of the nitride semiconductor layer, ~~and then~~ wherein the cleavage guide grooves are formed by scribing from bottom surfaces of the cleavage assist grooves.

39. (Currently Amended) ~~[[A]]~~ The method of fabricating a nitride semiconductor device ~~as claimed in~~ of claim 38, wherein a ~~depth~~ distance from the top surface of the nitride semiconductor wafer to a deepest end of the cleavage guide grooves is ~~within a range~~  $1 \leq d \leq$  equal to or larger than  $1 \mu\text{m}$  and equal to or smaller than  $10 \mu\text{m}$ .

40. (Currently Amended) ~~[[A]]~~ The method of fabricating a nitride semiconductor device ~~as claimed in~~ of claim 39, wherein the forming of the cleavage guide grooves ~~[[are]]~~ is such that the cleavage guide grooves are discontinuous in a same broken line with an equal interval ~~formed with intervals of 1 mm or shorter left between every two adjacent ones thereof on a same broken line.~~

41-48. (Cancelled)

49. (Currently Amended) ~~[[A]]~~ The method of fabricating a nitride semiconductor device ~~as claimed in~~ of claim 26, further comprising ~~the step of: before the step of cleaving the nitride semiconductor wafer,~~ forming cleavage assist grooves in a bottom surface of the nitride semiconductor wafer by scribing from below the nitride semiconductor substrate, ~~wherein the cleavage guide grooves and the cleavage assist grooves are so formed that the cleavage guide grooves are located along center axes of the cleavage assist grooves,~~ prior to the cleaving of the nitride semiconductor wafer.

50. (Currently Amended) ~~[[A]]~~ The method of fabricating a nitride semiconductor device ~~as claimed in~~ of claim 49, wherein the substrate ~~[[is]]~~ comprises a nitride semiconductor substrate ~~formed out of~~ comprising ~~[[a]]~~ another compound containing a group III element and nitrogen.

51. (Currently Amended) ~~[[A]]~~ The method of fabricating a nitride semiconductor device ~~as claimed in~~ of claim 49, wherein a ~~depth~~ distance from the top surface of the nitride semiconductor wafer to a deepest end of the cleavage guide grooves is ~~within a range  $1 \leq d \leq$~~  equal to or larger than 1  $\mu$ m and equal to or smaller than 10  $\mu$ m.

52. (Currently Amended) ~~[[A]]~~ The method of fabricating a nitride semiconductor device ~~as claimed in~~ of claim 51, wherein the forming of the cleavage guide grooves ~~[[are]]~~ is such that the cleavage guide grooves are discontinuous in a same broken line with an equal

interval ~~formed with intervals of 1 mm or shorter left between every two adjacent ones thereof on a same broken line.~~

53-60. (Cancelled)

61. (Currently Amended) [[A]] The method of fabricating a nitride semiconductor device as claimed in of claim 49, wherein, when a semiconductor layer of a material that cleaves in a different direction from the nitride semiconductor is formed at an interface between the nitride semiconductor layer and the substrate, further comprising forming [[first]] a plurality of cleavage assist grooves are formed in a shape of discontinuous broken lines in [[a]] the top surface of the nitride semiconductor [[layer]] wafer so as to a depth reaching reach half a thickness of the nitride semiconductor layer by scribing from above the top surface of the nitride semiconductor layer, and then wherein the cleavage guide grooves are formed by scribing from bottom surfaces of the cleavage assist grooves.

62. (Currently Amended) [[A]] The method of fabricating a nitride semiconductor device as claimed in of claim 61, wherein a ~~depth~~ distance from the top surface of the nitride semiconductor wafer to a deepest end of the cleavage guide grooves is within a range  $1 \leq d \leq$  equal to or larger than 1  $\mu\text{m}$  and equal to or smaller than 10  $\mu\text{m}$ .

63. (Currently Amended) [[A]] The method of fabricating a nitride semiconductor device as claimed in of claim 62, wherein the forming of the cleavage guide grooves [[are]] is such that the cleavage guide grooves are discontinuous in a same broken line with an equal interval formed with intervals of 1 mm or shorter left between every two adjacent ones thereof on a same broken line.

64-71. (Cancelled)

72. (Currently Amended) [[A]] The method of fabricating a nitride semiconductor device as claimed in of claim 26, wherein the forming of the cleavage guide grooves [[are]] is such that the cleavage guide grooves are discontinuous in a same broken line with an equal

~~interval formed with intervals of 1 mm or shorter left between every two adjacent ones thereof on a same broken line.~~

73. (Currently Amended) ~~[[A]]~~ The method of fabricating a nitride semiconductor device ~~as claimed in~~ of claim 26, wherein the at least one cleavage guide ~~grooves are~~ groove is formed ~~in every interval~~ between ~~[[the]]~~ any two neighboring stripe-shaped optical waveguides ~~[[on]]~~ along a same broken line of the cleavage guide grooves.

74-75. (Cancelled)

76. (Currently Amended) A method of fabricating a nitride semiconductor device, comprising ~~the steps of:~~

~~adjusting to within a range from 80 to 160  $\mu$ m a thickness of~~ forming a nitride semiconductor wafer ~~formed by depositing on a substrate that exhibits cleavage a nitride semiconductor layer formed out of~~ comprising a compound containing a group III element and nitrogen and ~~including,~~ having a cleavage plane crystallographically similar ~~[[equal]]~~ to a cleavage plane of the substrate~~[[, with]]~~ and comprising a plurality of stripe-shaped optical waveguides formed at an equal intervals separation in the nitride semiconductor layer;

adjusting a thickness of the nitride semiconductor wafer so that the thickness falls within a range from 80 to 160  $\mu$ m;

forming a plurality of cleavage guide grooves in a shape of discontinuous broken lines in a bottom surface of the nitride semiconductor wafer by scribing from below the substrate so that no cleavage guide groove extends under the stripe-shaped optical wave guides; and

cleaving the nitride semiconductor wafer along the cleavage guide grooves;

~~wherein the cleavage guide grooves are formed elsewhere than right below the stripe-shaped optical waveguides.~~

77. (Currently Amended) ~~[[A]]~~ The method of fabricating a nitride semiconductor device ~~as claimed in~~ of claim 76, wherein the substrate ~~[[is]]~~ comprises a nitride semiconductor substrate ~~formed out of~~ comprising ~~[[a]]~~ another compound containing a group III element and nitrogen.

78-82. (Cancelled)

83. (Currently Amended) ~~[[A]]~~ The method of fabricating a nitride semiconductor device ~~as claimed in~~ of claim 76, wherein the forming of the cleavage guide grooves ~~[[are]]~~ is such that the cleavage guide grooves are discontinuous in a same broken line with an equal interval ~~formed with intervals of 1 mm or shorter left between every two adjacent ones thereof on a same broken line.~~

84-86. (Cancelled)